

PSMN4R0-25YLC

N-channel 25 V 4.5 m Ω logic level MOSFET in LFPAK

Rev. 01 — 2 December 2010

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising Superjunction technology
- Ultra low QG, QGD & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing

- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	25	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see Figure 1	-	-	84	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	61	W
T _j	junction temperature		-55	-	175	°C
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{ or } 12}$	-	4.5	5.8	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 20 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 12}}{ or signs of the sign of the s$	-	3.5	4.5	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic c	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A};$ V_{DS} 12 V; see Figure 14; see Figure 15	-	3.5	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{see } \underline{\text{Figure } 14};$ $\text{see } \underline{\text{Figure } 15}$	-	10.9	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		。(巨木)
4	G	gate	[q]	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R0-25YLC	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _i ≥ 25 °C; T _i ≤ 175 °C	-	25	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	25	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	84	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{see } \frac{\text{Figure 1}}{\text{Model}}$	-	60	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; see Figure 4	-	336	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	61	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	200	-	V
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	55	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	336	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 84 A; $V_{sup} \le$ 25 V; R_{GS} = 50 Ω; unclamped; see Figure 3	-	17.4	mJ

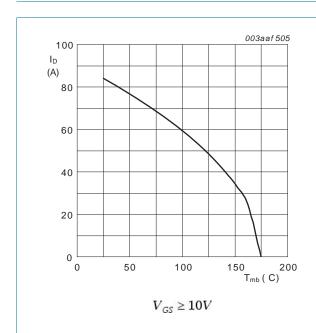
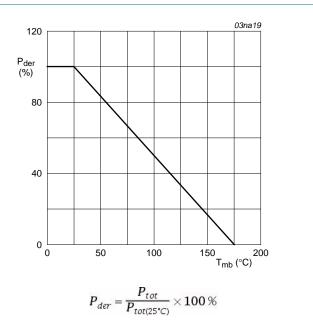


Fig 1. Continuous drain current as function of mounting base temperature



ig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN4R0-25YLC

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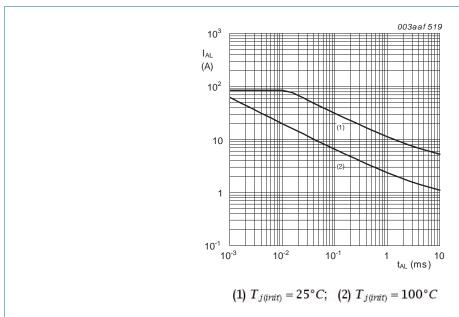


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

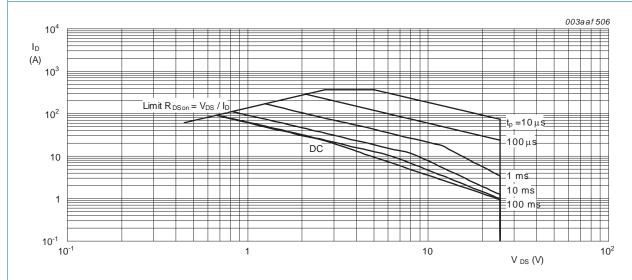
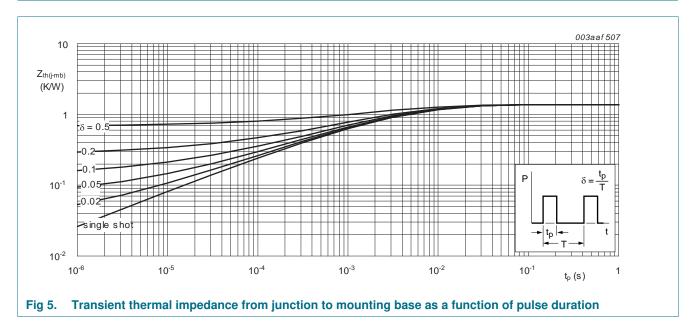


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	1.4	2.4	K/W



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	25	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	22.5	-	-	V
$\begin{array}{c} V_{GS(th)} & \text{gate-source thres} \\ & \text{voltage} \end{array}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 10	1.05	1.53	1.95	V
		I_D = 10 mA; V_{DS} = V_{GS} ; T_j = 150 °C; see <u>Figure 11</u>	0.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 11	-	-	2.25	V
I_{DSS}	drain leakage current	V_{DS} = 25 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μΑ
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nΑ
R _{DSon} drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	4.5	5.8	mΩ	
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	9.85	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	3.5	4.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	7.65	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	2.1	4.2	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 20 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	22.8	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	21.1	-	nC
		$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	10.9	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	3.3	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	2.25	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	1.05	-	nC
Q_{GD}	gate-drain charge	$I_D = 20 \text{ A}$; V_{DS} 12 V; $V_{GS} = 4.5 \text{ V}$; see Figure 14; see Figure 15	-	3.5	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.58	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1407	-	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}\text{C}$; see Figure 16	-	354	-	pF
C _{rss}	reverse transfer capacitance		-	119	-	pF

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	15.9	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	17.5	-	ns
$t_{d(off)}$	turn-off delay time		-	24	-	ns
t _f	fall time		-	9.9	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 ^{\circ}\text{C}$	-	7.32	-	nC
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.1	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	24.5	-	ns
Qr	recovered charge	V _{DS} = 12 V	-	16.1	-	nC
ta	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 20 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 12 \text{ V; see } \frac{\text{Figure } 18}{\text{Figure } 18}$	-	14.9	-	ns
t _b	reverse recovery fall time		-	9.6	-	ns

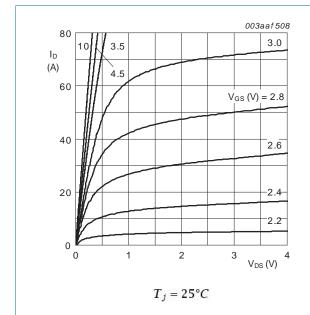


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

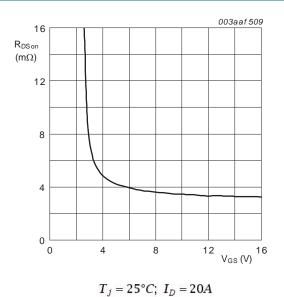


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

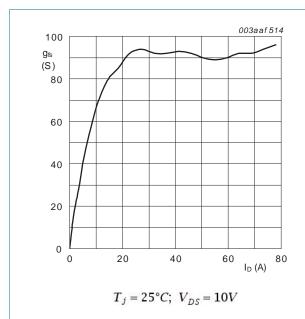


Fig 8. Forward transconductance as a function of drain current; typical values

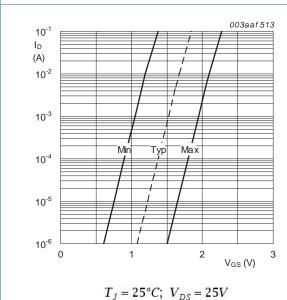


Fig 10. Sub-threshold drain current as a function of gate-source voltage

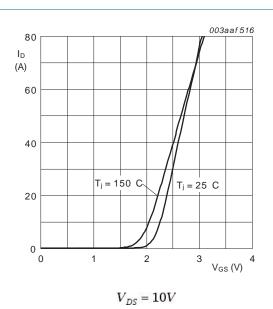


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

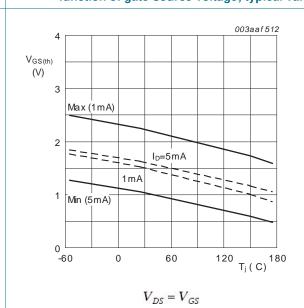


Fig 11. Gate-source threshold voltage as a function of junction temperature

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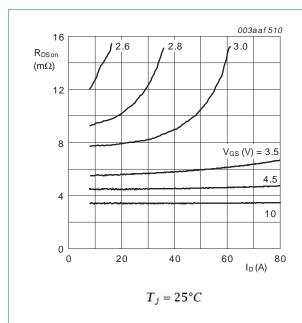


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

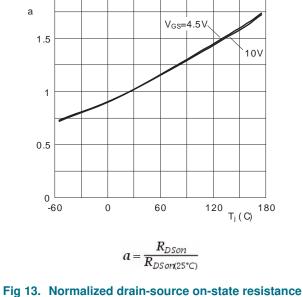


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

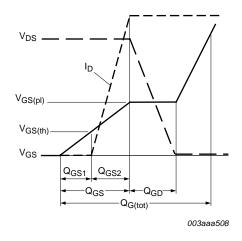
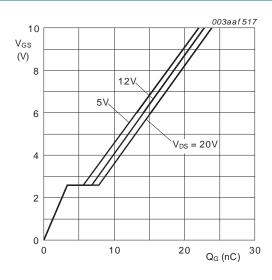


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 20A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

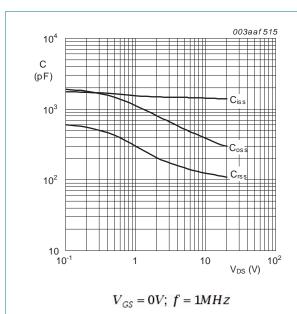


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

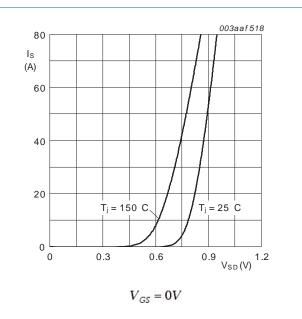


Fig 17. Source current as a function of source-drain voltage; typical values

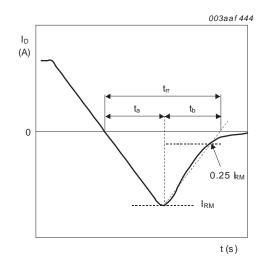


Fig 18. Reverse recovery timing definition

7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669

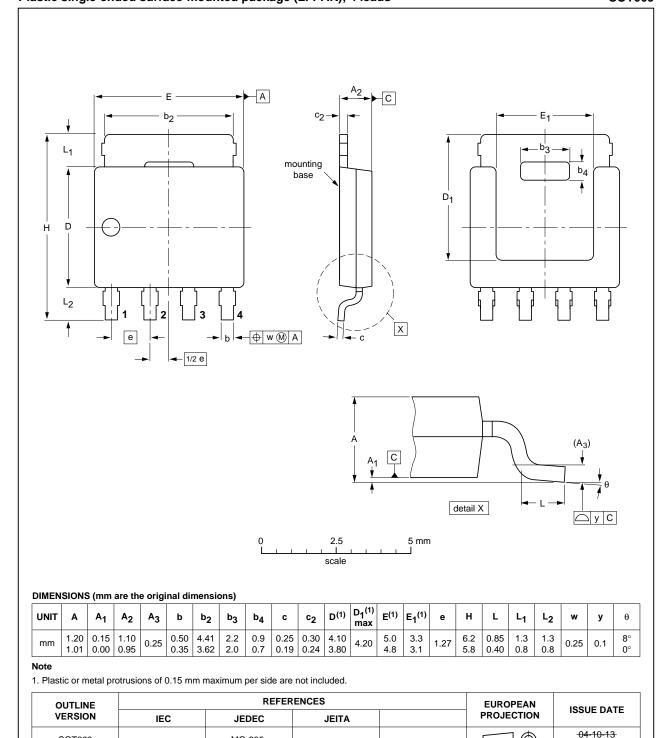


Fig 19. Package outline SOT669 (LFPAK)

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06-03-16

SOT669

PSMN4R0-25YLC

N-channel 25 V 4.5 mΩ logic level MOSFET in LFPAK

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R0-25YLC v.1	20101202	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel 25 V 4.5 m Ω logic level MOSFET in LFPAK

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